

Docket No.: 60188-131



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Kyoko HIRATA, et al.

: Attn: APPLICATIONS BRANCH

Serial No.: 10/009,842

Filed: December 17, 2001

For: SEMICONDUCTOR DEVICE

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SUPPLEMENTAL PRELIMINARY AMENDMENT

Hon. Assistant Commissioner for Patents
Washington, DC 20231

Sir:

Prior to examination of the above-referenced application, please amend the application as follows:

IN THE SPECIFICATION:

1. Please replace the paragraph beginning at page 3, line 24, continuing on to page 4, with the following rewritten paragraph:

6¹
--The P⁺ diffusion region **122** and the N⁺ diffusion region **112** are formed in the N-well region **130**, and a pn junction is formed on a junction face between the P⁺ diffusion region **122** and the N-well region **130**. Therefore, a diode can be constituted by using the P⁺ diffusion region **122** as an anode and the N⁺ diffusion region **112** as a cathode. In the diode element **1000**, one diode includes a junction of a pair of p and n, and therefore as the pn junction area (i.e., the bottom area of the P⁺ diffusion region **122**) increases, the current capacity of the diode element